



BSS138DW

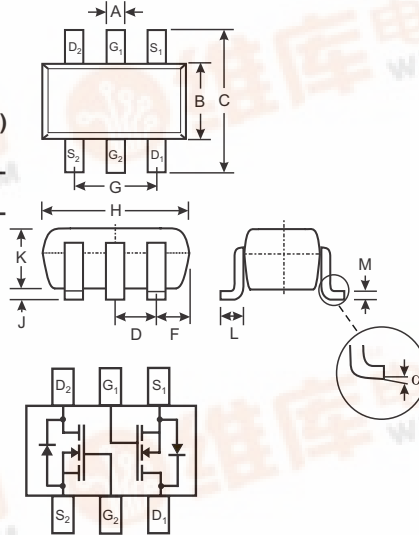
DUAL N-CANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Available in Lead Free/RoHS Compliant Version (Note 4)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Also Available in Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe). Please see Ordering Information, Note 6, on Page 2
- Terminal Connections: See Diagram
- Marking Code (See Page 2): K38
- Ordering & Date Code Information: See Page 2
- Weight: 0.006 grams (approximate)



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	0°	8°
All Dimensions in mm		

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	BSS138DW	Units
Drain-Source Voltage	V _{DS}	50	V
Drain-Gate Voltage (Note 3)	V _{DGR}	50	V
Gate-Source Voltage	V _{GSS}	±20	V
Drain Current (Note 1)	I _D	200	mA
Total Power Dissipation (Note 1)	P _d	200	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)						
Drain-Source Breakdown Voltage	BV _{DS}	50	75	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	0.5	μA	V _{DS} = 50V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 2)						
Gate Threshold Voltage	V _{GS(th)}	0.5	1.2	1.5	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	1.4	3.5	Ω	V _{GS} = 10V, I _D = 0.22A
Forward Transconductance	g _{FS}	100	—	—	mS	V _{DS} = 25V, I _D = 0.2A, f = 1.0KHz
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	—	50	pF	V _{DS} = 10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C _{rss}	—	—	8.0	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	—	—	20	ns	V _{DD} = 30V, I _D = 0.2A, R _{GEN} = 50Ω
Turn-Off Delay Time	t _{D(OFF)}	—	—	20	ns	

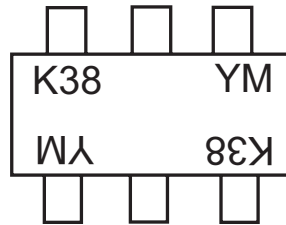
Note: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
2. Short duration test pulse used to minimize self-heating effect.

Ordering Information (Note 5)

Device	Packaging	Shipping
BSS138DW-7	SOT-363	3000/Tape & Reel

- Notes: 5. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.
6. For Lead Free/RoHS Compliant version part number, please add "-F" suffix to the part number above. Example: BSS138DW-7-F.

Marking Information

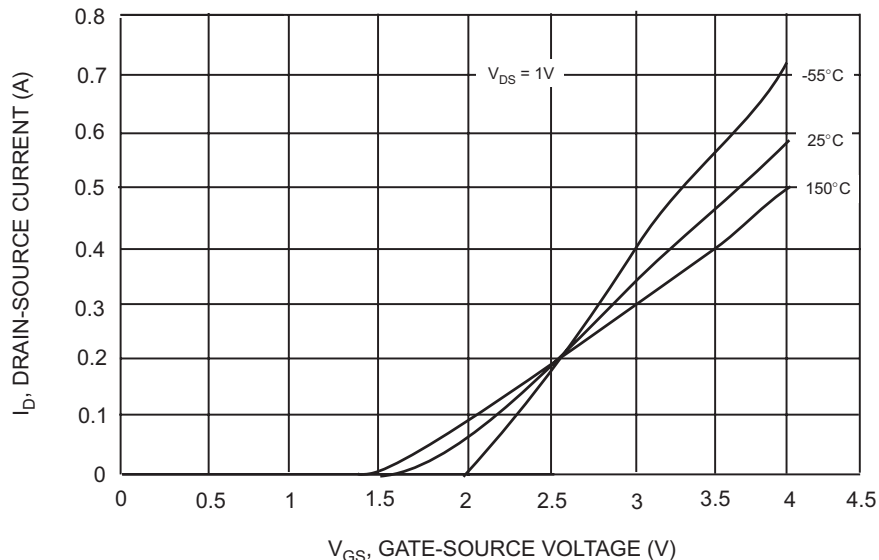
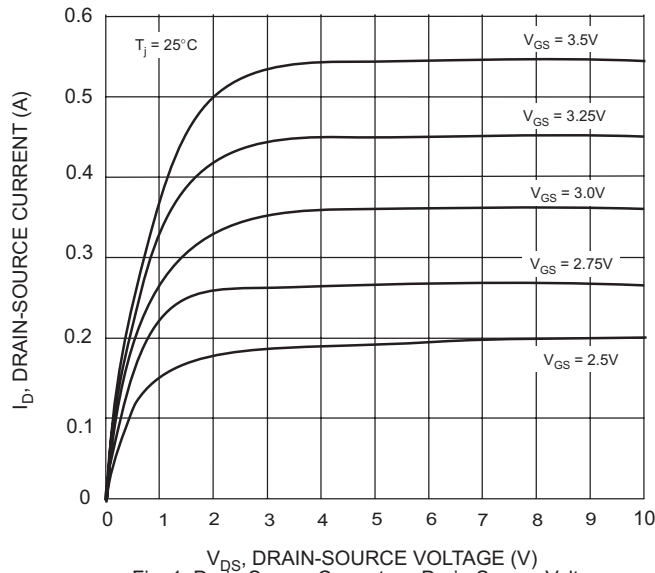


K38 = Product Type Marking Code
YM = Date Code Marking
Y = Year ex: N = 2002
M = Month ex: 9 = September

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	J	K	L	M	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D



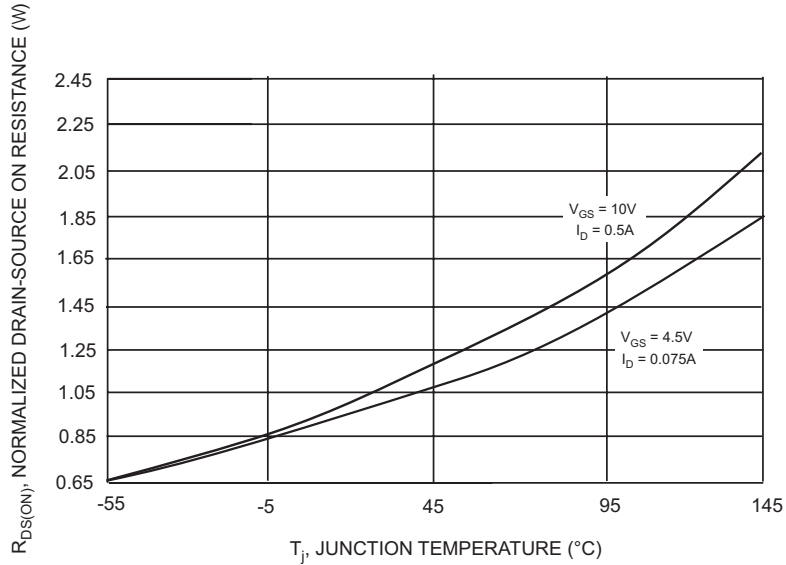


Fig. 3 Drain-Source On Resistance vs. Junction Temperature

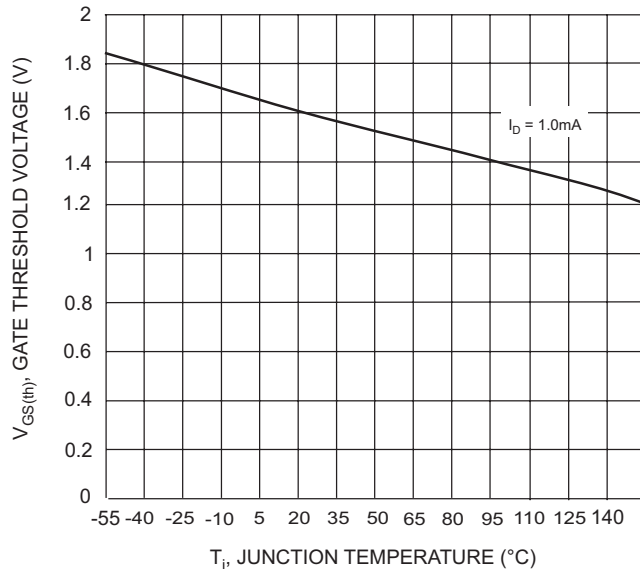


Fig. 4 Gate Threshold Voltage vs. Junction Temperature

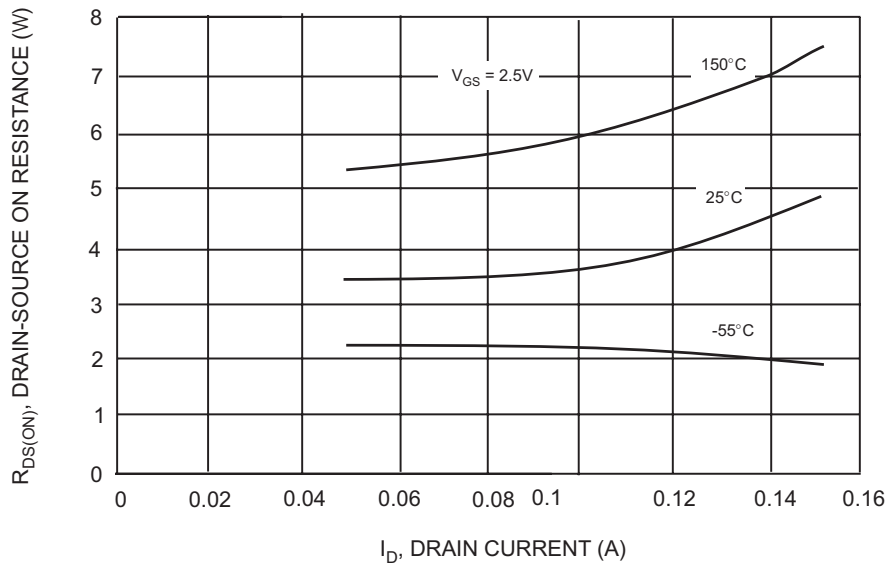


Fig. 5 Drain-Source On Resistance vs. Drain Current

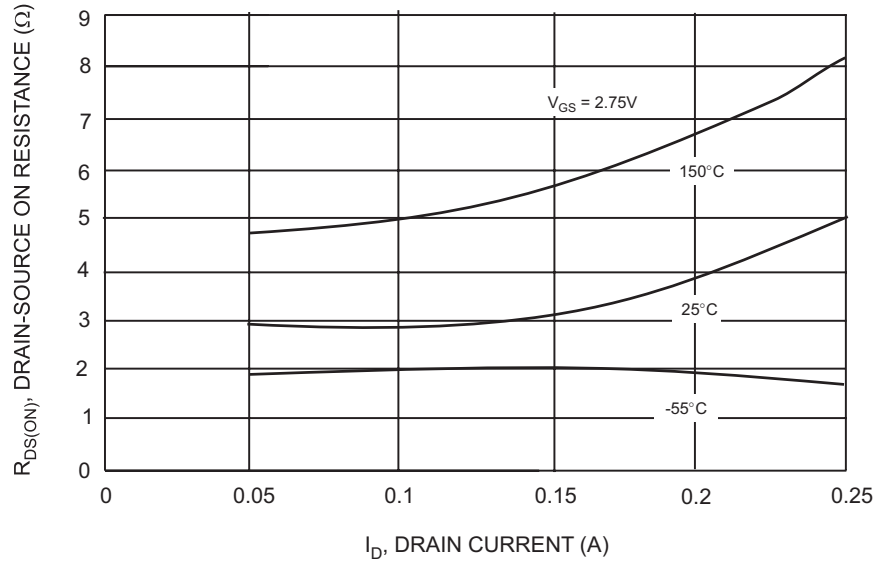


Fig. 6 Drain-Source On Resistance vs. Drain Current

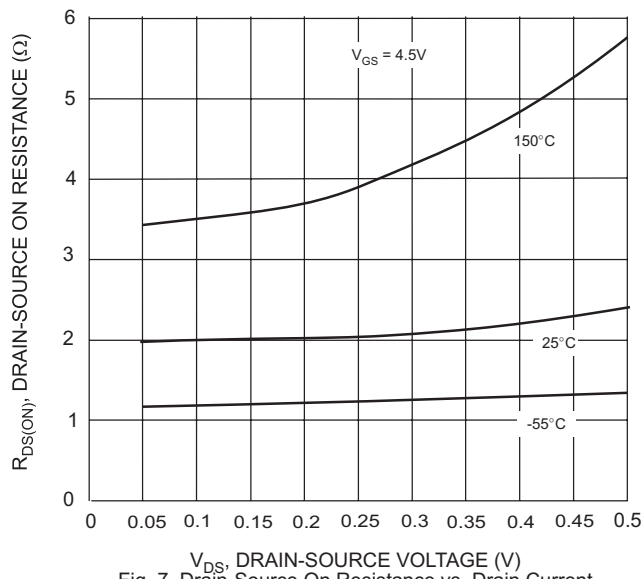


Fig. 7 Drain-Source On Resistance vs. Drain Current

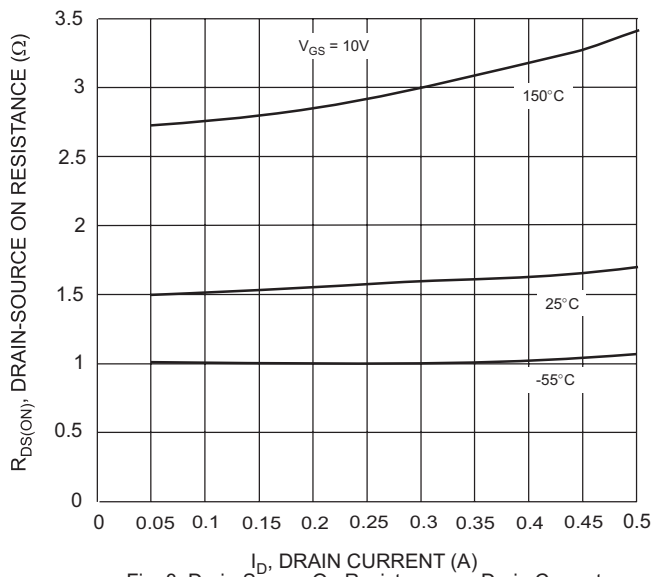


Fig. 8 Drain-Source On Resistance vs. Drain Current

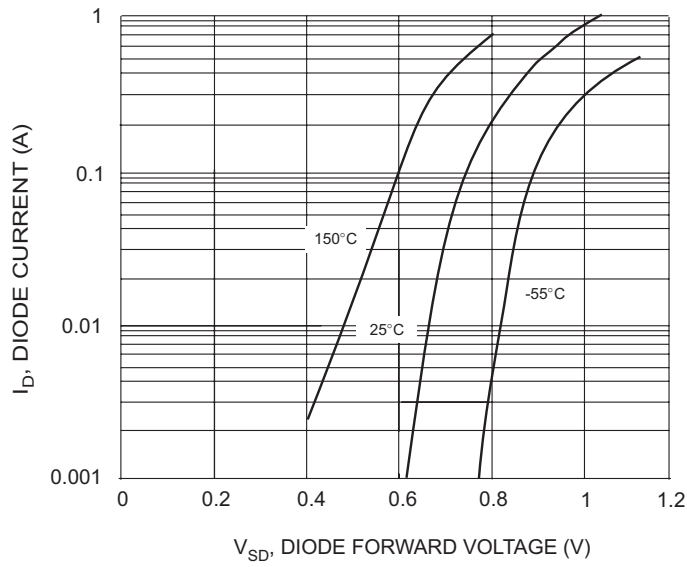


Fig. 9 Body Diode Current vs. Body Diode Voltage

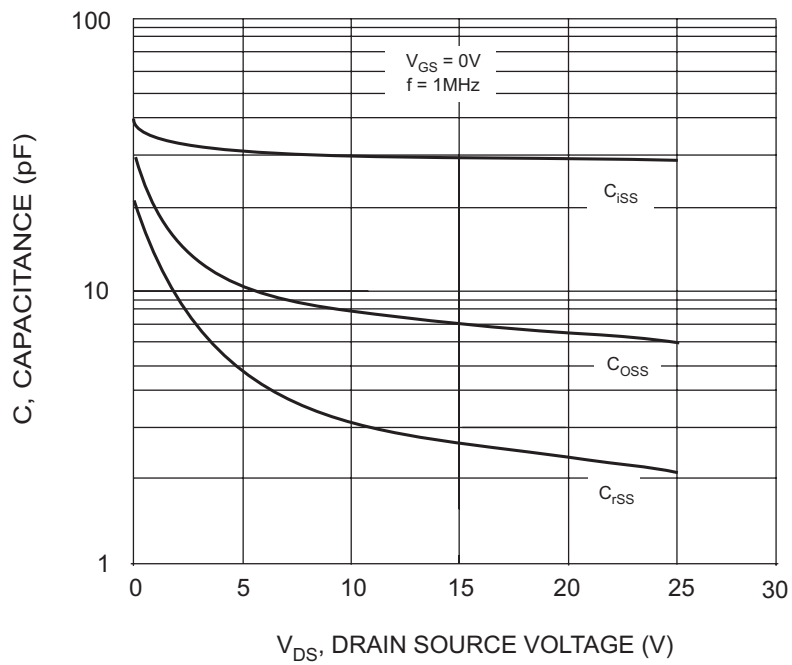


Fig. 10 Capacitance vs. Drain Source Voltage